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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/815,370	04/01/2004	Chih Chieh Yeh	MXIC 1571-1	8260
22470 7	590 12/29/2005		EXAMINER	
HAYNES BEFFEL & WOLFELD LLP			PHAN, TRONG Q	
P O BOX 366 HALF MOON BAY, CA 94019			ART UNIT	PAPER NUMBER
milli moon	2111, 011 > 1012		2827	
			DATE MAILED: 12/29/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
	10/815,370	YEH ET AL.			
Office Action Summary	Examiner	Art Unit			
	TRONG PHAN	2827			
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with t	he correspondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period was a failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICAT 16(a). In no event, however, may a reply rill apply and will expire SIX (6) MONTHS cause the application to become ABAND	FION.  be timely filed  from the mailing date of this communication.  DONED (35 U.S.C. § 133).			
Status					
1) ⊠ Responsive to communication(s) filed on 29 Ju 2a) □ This action is FINAL. 2b) ⊠ This 3) □ Since this application is in condition for allowan closed in accordance with the practice under E	action is non-final. ice except for formal matters	•			
Disposition of Claims					
4) ☐ Claim(s) 1-65 is/are pending in the application. 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-65 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	vn from consideration.				
Application Papers					
9) ☐ The specification is objected to by the Examine	r.				
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correcti  11) The oath or declaration is objected to by the Ex					
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Applity documents have been rec (PCT Rule 17.2(a)).	ication No ceived in this National Stage			
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 8/9/05.	Paper No(s)/M	mary (PTO-413) ail Date nal Patent Application (PTO-152)			

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Art Unit: 2827

## **DETAILED ACTION**

In view of the newly discovered art of Kobatake, 5,815,441, the allowance of claims 1-65 as set forth in the last office action of May 9, 2005 has been withdrawn.

A new non-final office action has been set forth as below:

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-65 are rejected under 35 U.S.C. 103(a) as being unpatentable over Walukas, 6,229,737, in view of Kobatake, 5,815,441, and Lin, 6,671,209.

Walukas, 6,229,737, discloses in Fig. 1 a memory device comprising: first memory array EEPROM 12 for storing a page of data (see lines 44-45, column 5) in response to a first interleaving algorithm (se lines 1-3, column 5); second flash memory array 14 for storing a data bite (see lines 39-42, column 6) in response to a second interleaving algorithm (see lines 3-6, column 5); processor CPU 24;

SRAM 22.

What is not shown in Walukas, 6,229,737, is the first and the second memory array on the same substrate as recited in claims 1, 21-23 and 45-46.

Kobatake, 5,815,441, discloses in Fig.1 the teaching of forming a first nonvolatile EEPROM 16 and a second nonvolatile Flash memory array 17 on the same substrate in

a single chip (see lines 30-48, column 2).

It would have been obvious under 35 USC 103(a) to one of ordinary skill in the art at the time of the invention was made to form first memory array EEPROM 12 and second flash memory array 14 in Fig. 1 of Walukas, 6,229,737, on the same substrate in a single chip as taught by Fig. 1 of Kobatake, 5,815,441, for the purpose of having low cost in which programs and data can be stored separately (see lines 30-34, column 2 of Kobatake, 5,815,441).

What is not shown in Walukas, 6,229,737, which is modified by Kobatake, 5,815,441, is the charge storage non-volatile memory cells as recited in claims 2-20, 24-44 and 47--65.

Lin, 6,671,209, discloses in Fig. 1 a memory cell which can be used for EEPROM and Flash memory devices (see lines 18-43, column 1) comprising: substrate 10;

charge trapping layer 16 of silicon nitride;

first tunneling oxide layer 14;

second dielectric layer 18;

gate electrode 20;

source channel region 22;

drain channel region 24;

erasing by band-to-band hot electron/holes/electric field injection (see lines 44-51,

column 1 and lines 31-32, column 2);

two-bit per single cell (see lines 17-20, column 2).

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It would have been obvious under 35 USC 103(a) to one of ordinary skill in the art at the time of the invention was made to utilize the memory cell in Fig. 1 of Lin, 6,671,209, for the EEPROM array 12 and the Flash memory array 14 in Fig. 1 of Walukas et al., 6,229,737, which is modified by Kobatake, 5,815,441, for the purpose of preventing drain leakage current and reducing power consumption (see lines 11-17, column 2 of Lin, 6,671,209).

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to TRONG PHAN whose telephone number is (571) 272-1794. The examiner can normally be reached on M-F (8:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zabrabian can be reached on (571)272-1851. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TRONG PHAN
PRIMARY EXAMINER